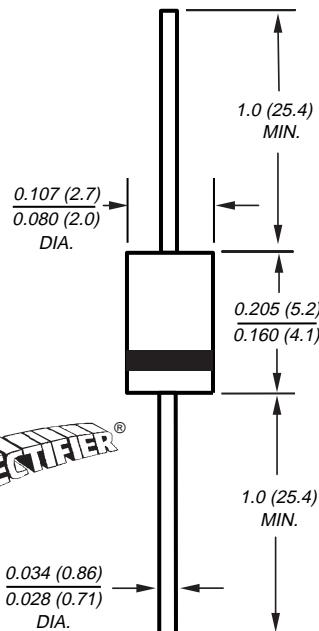




Glass Passivated Ultrafast Rectifier

 Reverse Voltage 50 to 400V
 Forward Current 1.0A

DO-204AL (DO-41)


Dimensions in inches and (millimeters)

*Glass Encapsulation technique is covered by
 Patent No. 3,996,602, brazed-lead assembly to Patent No. 3,930,306

Features

- Plastic package has Underwriters Laboratories Flammability Classification 94V-0
- Cavity-free glass passivated junction
- Ultrafast recovery time for high efficiency
- Low forward voltage, high current capability
- Low leakage current
- High surge current capability
- High temperature metallurgically bonded construction
- High temperature soldering guaranteed:
 300°C/10 seconds, 0.375" (9.5mm) lead length,
 5 lbs. (2.3kg) tension

Mechanical Data

Case: JEDEC DO-204AL, molded plastic over solid glass body

Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.012 oz., 0.3 g

Maximum Ratings & Thermal Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	EGP10A	EGP10B	EGP10C	EGP10D	EGP10F	EGP10G	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	V
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	V
Maximum DC blocking voltage	V _D	50	100	150	200	300	400	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at TA = 55°C	I _{F(AV)}					1.0		A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}				30			A
Typical thermal resistance (Note 1)	R _{θJA}			50				°C/W
Operating and storage temperature range	T _{J,TSTG}				−65 to +150			°C

Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	EGP10A	EGP10B	EGP10C	EGP10D	EGP10F	EGP10G	Unit
Maximum instantaneous forward voltage at 1.0A	V _F		0.95			1.25		V
Maximum DC reverse current at rated DC blocking voltage	I _R			5.0				µA
TA = 25°C TA = 125°C				100				
Maximum reverse recovery time at I _F = 0.5A, I _R = 1.0A, I _{rr} = 0.25A	t _{rr}			50				ns
Typical junction capacitance at 4.0V, 1MHz	C _J		22			15		pF

Note: (1) Thermal resistance from junction to ambient, and from junction to lead at 0.375" (9.5mm) lead length, P.C.B. mounted

EGP10A thru EGP10G



Vishay Semiconductors
formerly General Semiconductor

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Maximum Forward Current Derating Curve

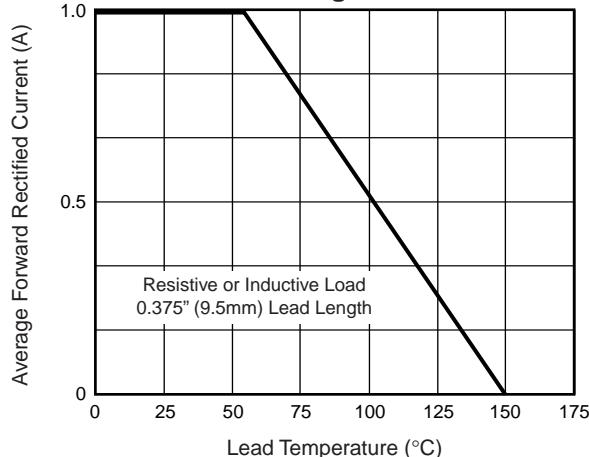


Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current

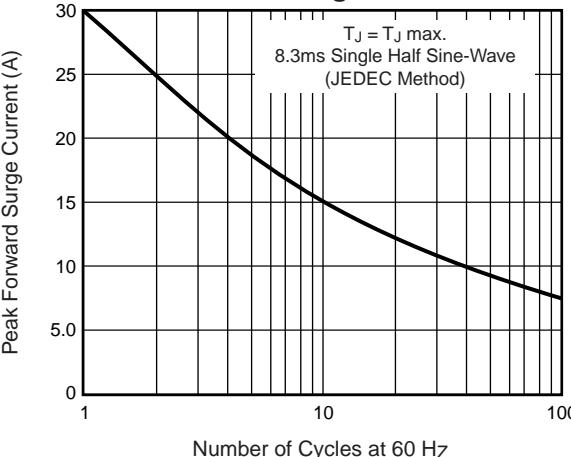


Fig. 3 – Typical Instantaneous Forward Characteristics

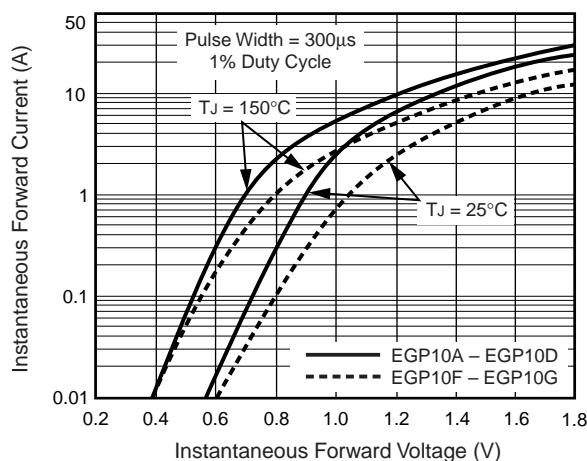


Fig. 4 – Typical Reverse Leakage Characteristics

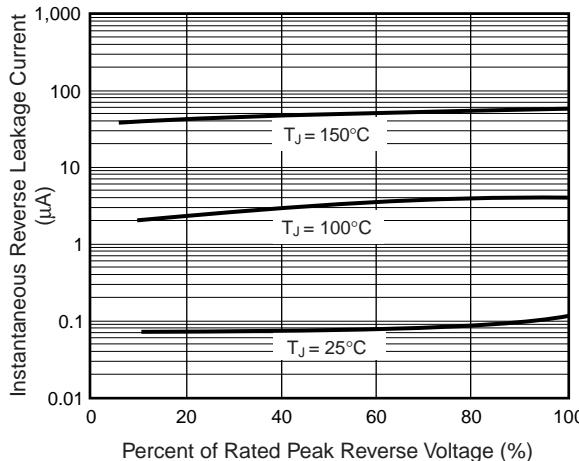


Fig. 5 – Typical Junction Capacitance

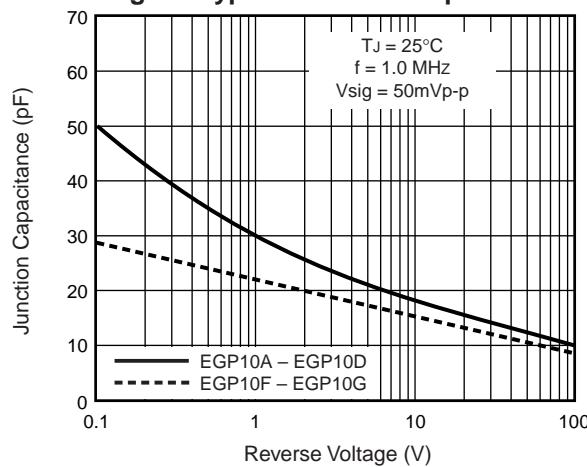


Fig. 6 – Typical Transient Thermal Impedance

